

Fausto Fantini

List of Publications by Year in descending order

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18
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1307366

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docs citations

18
times ranked

313
citing authors

#	ARTICLE	IF	CITATIONS
1	Electromigration in thin-film interconnection lines: models, methods and results. Materials Science and Engineering Reports, 1991, 7, 143-220.	5.8	131
2	Investigation of High-Electric-Field Degradation Effects in AlGaIn/GaN HEMTs. IEEE Transactions on Electron Devices, 2008, 55, 1592-1602.	1.6	110
3	Metal-GaAs interaction and contact degradation in microwave MESFETs. Quality and Reliability Engineering International, 1990, 6, 29-46.	1.4	26
4	Correlation between DC and rf degradation due to deep levels in AlGaIn/GaN HEMTs. , 2009, , .		26
5	Analysis of GaN HEMT Failure Mechanisms During DC and Large-Signal RF Operation. IEEE Transactions on Electron Devices, 2012, 59, 1385-1392.	1.6	20
6	Reliability problems with VLSI. Microelectronics Reliability, 1984, 24, 275-296.	0.9	14
7	Introduction to the Special Issue on GaN and Related Nitride Compound Device Reliability. IEEE Transactions on Device and Materials Reliability, 2008, 8, 239-239.	1.5	12
8	Cathodoluminescence evidence of stress-induced outdiffusion of beryllium in AlGaAs/GaAs heterojunction bipolar transistors. Journal Physics D: Applied Physics, 1998, 31, 3004-3008.	1.3	10
9	Reliability of compound semiconductor devices. Microelectronics Reliability, 1992, 32, 1559-1569.	0.9	7
10	Experimental and simulated dc degradation of GaN HEMTs by means of gate-drain and gate-source reverse bias stress. Microelectronics Reliability, 2010, 50, 1523-1527.	0.9	5
11	Thermal stability of gate HEMT's. Microelectronics Reliability, 1995, 35, 631-635.	0.9	4
12	Life tests and field results of GaAs FETs. Annales Des Telecommunications/Annals of Telecommunications, 1990, 45, 617-624.	1.6	2
13	VLSI reliability: Contributions from a three year national research program. European Transactions on Telecommunications, 1990, 1, 209-220.	1.2	2
14	On the Astm electromigration test structure applied to Al _{0.1} Si/TiN/Ti bamboo metal lines. Quality and Reliability Engineering International, 1995, 11, 33-39.	1.4	2
15	Study of GaN HEMTs electrical degradation by means of numerical simulations. , 2010, , .		2
16	Design and simulation of a test pattern for three-dimensional latch-up analysis. Microelectronics Journal, 1993, 24, 759-771.	1.1	0
17	An Investigation of the Electrical Degradation of GaN High-Electron-Mobility Transistors by Numerical Simulations of DC Characteristics and Scattering Parameters. Journal of Electronic Materials, 2011, 40, 362-368.	1.0	0
18	Degradation mechanisms in heterostructure devices and their correlation with defects. , 2017, , 503-514.		0